



# **Sonic Fast Recovery Diode**

 $V_{RRM} = 3300 V$ 

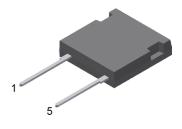
 $I_{F80} = 50 A$ 

 $t_{rr} = 1650 \, \text{ns}$ 

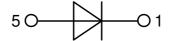
High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

Part number

## DHG55I3300FE



Backside: isolated see important note page 3



### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

## **Applications:**

- Antiparallel diode for high frequency switching devices
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

## Package: i4-Pac

- Isolation Voltage: 4200 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- · Reduced weight
- Advanced power cycling

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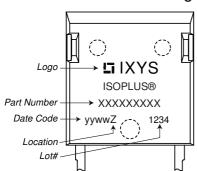
Fast Diode					Ratings	ngs			
Symbol	Definition	Conditions		min.	typ.	max.	Unit		
V <sub>RSM</sub>	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			3300	V		
$V_{RRM}$	max. repetitive reverse blocking ve	oltage	$T_{VJ} = 25^{\circ}C$			3300	V		
I <sub>R</sub>	reverse current, drain current	V <sub>R</sub> = 3300 V	$T_{VJ} = 25^{\circ}C$			100	μΑ		
		$V_R = 3300 \text{ V}$	$T_{VJ} = 125^{\circ}C$			2	mΑ		
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 60 A	$T_{VJ} = 25^{\circ}C$			3.38	V		
		$I_F = 120 A$				4.35	٧		
		$I_F = 60 \text{ A}$	T <sub>VJ</sub> = 125°C			3.39	V		
		$I_F = 120 A$				4.70	٧		
I <sub>FAV</sub>	average forward current	$T_{c} = 80^{\circ}C$	$T_{VJ} = 150$ °C			50	Α		
		DC					1 1 1 1		
V <sub>F0</sub>	threshold voltage	an adadation only	T <sub>VJ</sub> = 150°C			2.50	V		
r <sub>F</sub>	slope resistance	ess calculation only				14.5	mΩ		
R <sub>thJC</sub>	thermal resistance junction to case	9				0.45	K/W		
R <sub>thCH</sub>	thermal resistance case to heatsin	nk			0.15		K/W		
P <sub>tot</sub>	total power dissipation		$T_{C} = 25^{\circ}C$			280	W		
I <sub>FSM</sub>	max. forward surge current	$t = 10 \text{ ms}$ ; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			600	Α		
CJ	junction capacitance	$V_R = 1800  V$ $f = 1  MHz$	$T_{VJ} = 25^{\circ}C$		16		pF		
I <sub>RM</sub>	max. reverse recovery current	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	T <sub>vJ</sub> = 25 °C		55		Α		
		$I_F = 60 \text{ A}; V_R = 1800 \text{ V}$	$T_{VJ} = 125$ °C		65		Α		
t <sub>rr</sub>	reverse recovery time	-di <sub>F</sub> /dt = 500 A/μs	$T_{VJ} = 25 ^{\circ}\text{C}$		1650		ns		
		)	$T_{VJ} = 125$ °C		2400		ns		





Package	i4-Pac			ı	Ratings	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal				70	Α
T <sub>VJ</sub>	virtual junction temperature			-40		150	°C
T <sub>op</sub>	operation temperature			-40		125	°C
T <sub>stg</sub>	storage temperature			-40		150	°C
Weight					5.5		g
<b>F</b> <sub>c</sub>	mounting force with clip			20		120	N
d <sub>Spp/App</sub>	creepage distance on surface	etriking dietanee through air	terminal to terminal	13.8			mm
$d_{Spb/Apb}$	creepage distance on surface	striking distance through an	terminal to backside	5.1			mm
V <sub>ISOL</sub>	isolation voltage	t = 1 second	50/00 II	4200			V
		t = 1 minute	50/60 Hz, RMS; IISOL ≤ 1 mA	2500			٧

## **Product Marking**



## Part description

D = Diode

H = Sonic Fast Recovery Diode

G = extreme fast

55 = Current Rating [A]

I = Single Diode

3300 = Reverse Voltage [V]

FE = i4-Pac (2HV)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG55l3300FE	DHG55I3300FE	Tube	25	516110

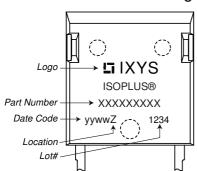
Equiva	lent Circuits for	Simulation	* on die level	$T_{VJ} = 150^{\circ}C$
$I \rightarrow V_0$	)—[R <sub>0</sub> ]	Fast Diode		
V <sub>0 max</sub>	threshold voltage	2.5		V
$R_{0 max}$	slope resistance *	14.5		$m\Omega$





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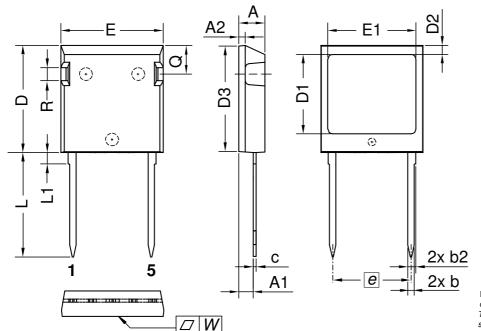
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#### Outlines i4-Pac



Dim.	Millimeter Inches		hes	
ווווט.	min	max	min	max
Α	4.83	5.21	0.190	0.205
A1	2.59	3.00	0.102	0.118
A2	1.17	2.16	0.046	0.085
b	1.14	1.40	0.045	0.055
b2	1.47	1.73	0.058	0.068
С	0.51	0.74	0.020	0.029
D	20.80	21.34	0.819	0.840
D1	14.99	15.75	0.590	0.620
D2	1.65	2.03	0.065	0.080
D3	20.30	20.70	0.799	0.815
Е	19.56	20.29	0.770	0.799
E1	16.76	17.53	0.660	0.690
е	15.24	BSC	0.600	BSC
L	19.81	21.34	0.780	0.840
L1	2.11	2.59	0.083	0.102
Q	5.33	6.20	0.210	0.244
R	2.54	4.57	0.100	0.180
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.05 mm über der Kunststoffoberläche der Bauteilunterseite The convexbow of substrate is typ. < 0.05 mm over plastic surface level ofdevice bottom side

## Important note:

External clearances between pins and between pins and tab may be insufficient to prevent flash over under all conditions. It is the customer's responsibility to apply additional insulation appropriate to the application.

ISOPLUS264 is designed to isolate a max continuous operation voltage (DC) of 1700 V. The peak test voltage of 4200 V assures safety for transient voltages only. The package is not tested for partial discharge.

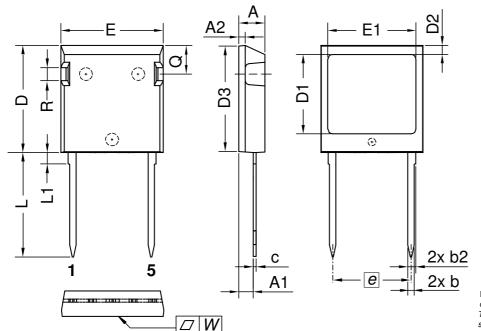
If the product is used outside the package design voltage range the customer must use additional electrical insulation. Extra insulation layers should be used both between the tab and any heatsink and between any conducting clip and the top surface of the package particularly when metal parts (such as a heatsink or a clip) are in contact. Please note that the intention of this package is to provide customers with an encapsulated die for high voltage application but the responsibility rests entirely with the customer to ensure for safe operation. Bodily injury cannot be excluded if this warning is disregarded. Device implementation is the end user's responsibility.

For a low FIT rate over lifetime failures due to SEB (Single Event Burnout) and an adequate voltage derating should be considered.





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